

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	142	(passivation protection dielectric) near8(manufactur\$5 method process\$4)near11 oxide and (sic silicon near carbide)near4 substrate	US-PGPUB; USPAT	OR	ON	2005/10/01 01:41
L2	76	(passivation protection dielectric) near8(manufactur\$5 method process\$4)near11 oxide and (sic silicon near carbide)near substrate	US-PGPUB; USPAT	OR	ON	2005/10/01 01:52
L3	171	(passivation protection)near5(dielectric oxide) and (sic silicon near carbide)near substrate	US-PGPUB; USPAT	OR	ON	2005/10/01 01:42
L4	123	(passivation)near5(dielectric oxide) and (sic silicon near carbide)near substrate	US-PGPUB; USPAT	OR	ON	2005/10/01 01:42
L5	27	(passivation)near5(dielectric oxide) near11(nitr\$5)and (sic silicon near carbide)near substrate	US-PGPUB; USPAT	OR	ON	2005/10/01 01:42
L6	9	(passivation protection)near15("sio.sub.2" near5 "Si.sub.3n.sub.4") and (sic silicon near carbide)near substrate	US-PGPUB; USPAT	OR	ON	2005/10/01 01:44
L7	31	(passivation protection)near15("sio.sub.2" near5 "Si.sub.3n.sub.4") and (sic silicon near carbide)	US-PGPUB; USPAT	OR	ON	2005/10/01 01:51
L8	22	7 not 6	US-PGPUB; USPAT	OR	ON	2005/10/01 01:46
L9	8	(nitrogen-oxygen nitrogen\$1oxygen nitrogen near oxygen "O.sub.2N.sub.2" nitric near oxide "O.sub.2N.sub.2") same ((passivation))and ((substrate\$2)near7((silicon) near9 (carbide carbon)))	US-PGPUB; USPAT	OR	OFF	2005/10/01 01:47
L10	137	(oxide silicon adj oxide "sio" "sio.sub.2")near13 (anneal\$4 heat\$4 beam\$2 temperat\$5)near5(nitrogen-oxygen nitrogen\$1oxygen nitrogen near oxygen "O.sub.2N.sub.2" nitric near oxide "O.sub.2N.sub.2")near9(atmosphere environment)	US-PGPUB; USPAT	OR	ON	2005/10/01 01:50
L11	13	10 and (sic silicon near carbide)	US-PGPUB; USPAT	OR	ON	2005/10/01 01:51

L12	56	(oxide silicon adj oxide "sio" "sio. sub.2")near13 (anneal\$4 heat\$4 beam\$2 temperat\$5)near5(nitrogen-oxygen nitrogen\$1oxygen nitrogen near oxygen "O.sub.2N.sub.2" nitric near oxide "O.sub.2N.sub.2")near9(atmosphere environment)	EPO; JPO; DERWENT	OR	ON	2005/10/01 01:51
L13	6	(passivation protection dielectric) and 12	EPO; JPO; DERWENT	OR	ON	2005/10/01 01:59
L14	13	(nitrogen-oxygen nitrogen\$1oxygen nitrogen near oxygen "O.sub.2N.sub.2" nitric near oxide "O.sub.2N.sub.2") and (passivation) and (silicon) near9 (carbide carbon)	USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/01 01:54
L15	302	(oxide silicon adj oxide "sio" "sio. sub.2")near13 (anneal\$4 heat\$4 beam\$2 temperat\$5)near5(atmosphere environment)and (carbide sic silicon near5 carbon)near7(substrate device\$2 element\$2)and (semiconductor\$2 transistor\$2)	US-PGPUB; USPAT	OR	ON	2005/10/01 01:56
L16	821	438/167 438/172 438/571.ccls.	US-PGPUB; USPAT	OR	ON	2005/10/01 01:58
L17	4	15 and 16	US-PGPUB; USPAT	OR	ON	2005/10/01 01:57
L18	1128	438/167 438/172 438/571.ccls.	EPO; JPO	OR	ON	2005/10/01 01:58
L19	0	(passivation protection) and 18 and sic	EPO; JPO; DERWENT	OR	ON	2005/10/01 01:59